



# **Investigations with Gaseous Electron Multipliers (GEM) for use on** the ISIS spallation neutron source

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#### Introduction

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## Investigations with S8900 GEMs

The Gaseous Electron Multiplier (GEM) technology promises to Encouraging though these results are, we see evidence for the (cont) deliver <sup>3</sup>He based neutron detectors for a wide range of applications GEMs 'charging up' over time (~20% gain rise over a period of 24 for ISIS. When coupled to the use of  $CF_4$  as a quench gas they hours, under continuous neutron illumination), which would need to could offer the potential for a 2D detector for neutrons with sub mm be addressed before incorporating detectors based on GEMs into Figure 5: Gain curves in various Ar: Isobutane gas mixtures from resolution. However, the operation of these devices at elevated CF<sub>4</sub> any of the ISIS instruments. We postulate that the gain increase of *S8900 GEM with 0.5mm holes* pressures has proved to be very problematic. Reducing the the GEM device is due to charge collecting on the (very small) induction gap between the GEM and the readout plane appears to kapton 'ridge' that is present at every GEM hole. We propose the Ar: IB 75:25 give an enhanced gain from the GEM detector which we have use of S8900 electron conducting glass as a solution to this 🔸 Ar:IB 80:20 <del>√ – – √</del> Ar:IB 85:15 employed in the detectors described here. charging, and attempted to make a GEM type structure on an - Ar:IB 90:10 + Ar:IB 95:5 S8900 substrate. The first devices were made by IMT in Switzerland using our standard 1mm thick glass. This is both rigid and Investigations with kapton GEMs manageable. The holes were put into the glass by using a laser Standard CERN GEMs with 50µm thick copper clad kapton foil, gain drilling technique. 10<sup>4</sup>

Investigations with S8900 GEMs

50µm holes patterned at 140µm hole pitch of 10mm by 10mm area have been used. The GEM foil is stretched and glued to an FR4 frame which is 1mm thick, which is also used to determine the investigated, one with 1mm diameter holes and one with 0.5mm induction gap to the readout electrode. The active gas region is formed by the addition of a drift plane placed 10mm above the GEM foil. This is housed in a pressure vessel which has been designed for a working pressure of 14bar.

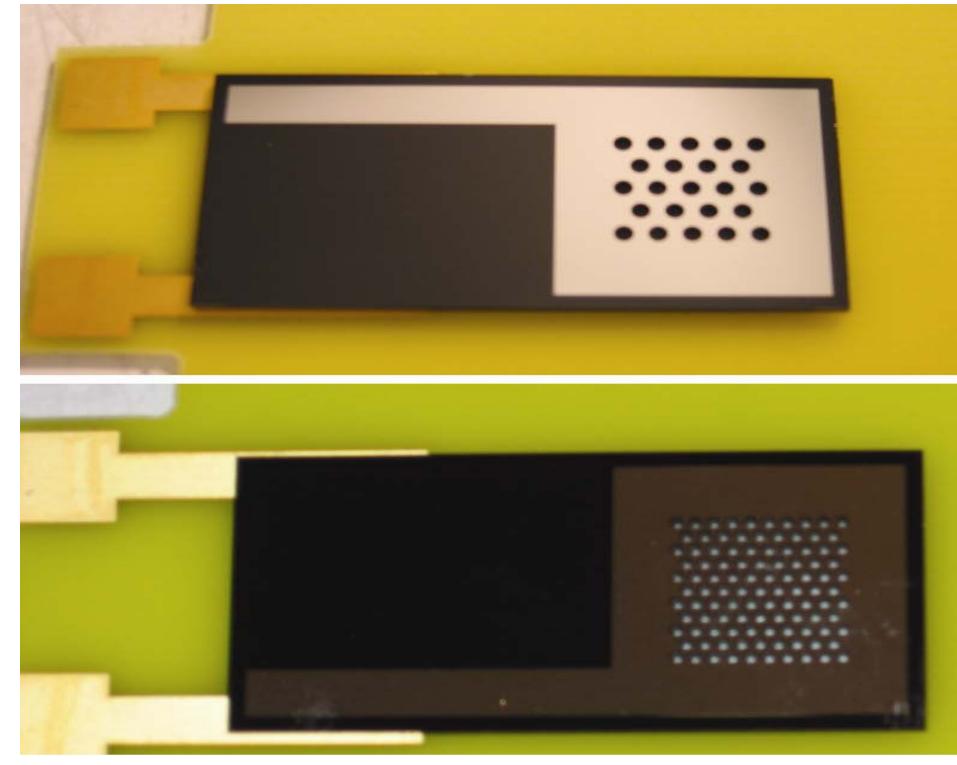
Initially filled with 0.5 bar of <sup>3</sup>He and 1.0 bar CF<sub>4</sub> (corresponding to a neutron detection efficiency of ~4% for 1Å neutrons) the vessel was illuminated with neutrons produced from a moderated <sup>241</sup>Am:Be source. The concentration of  $CF_4$  was then increased 0.5bar at a time and gain measurements were made in each mixture. Figure 1 shows the pulse height distribution obtained from the detector operating with 3 bars of  $CF_4$  at a gain of ~8.

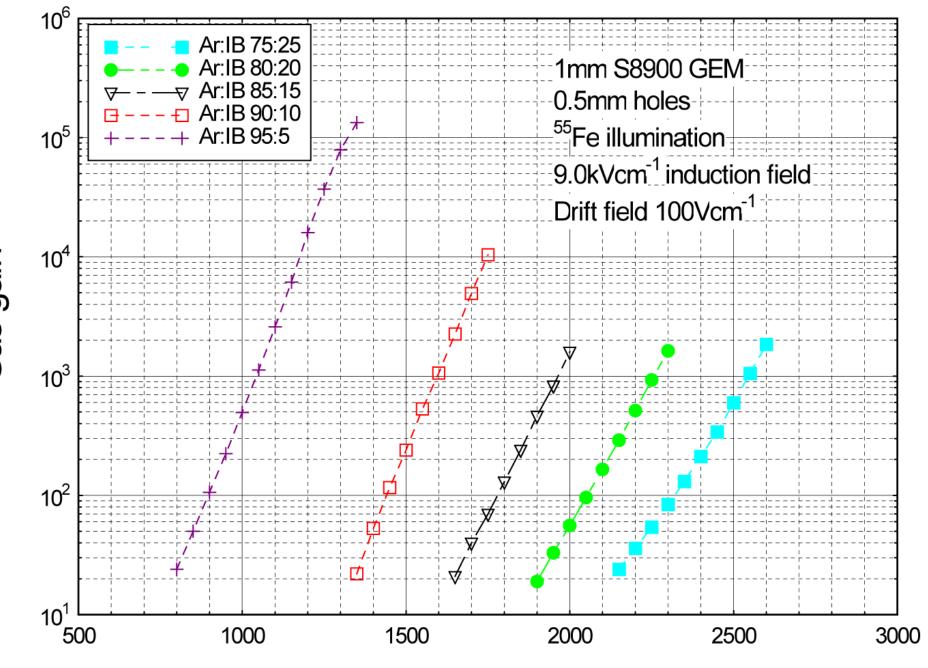
Figure 1: Pulse height distribution from <sup>241</sup>Am:Be neutron source obtained from a kapton GEM with 0.5 bar <sup>3</sup>He and 3 bars  $CF_4$ 

> <sup>3</sup>He:CF<sub>4</sub> 0.5bars:3.0bars 2000 second acquisition Vd-6kV, *Δ*V<sub>GEM</sub> -1020V

In the first batch of S8900 GEMs, two different geometries were diameter holes through the glass, both in a hexagonal array with an active area of 10 by 10mm. A chromium layer was then lithographically added to both sides of the glass, leaving 100µm of clearance around both hole sizes. The glass GEMs were mounted on carrier boards, see figure 3, enabling them to be easily incorporated into one of our current flowing gas vessels.

Figure 3: S8900 GEMs mounted on carrier boards; the top photo shows the GEM with the 1mm diameter holes and the bottom photo shows the GEM with 0.5mm diameter holes





Voltage difference across GEM,  $\Delta V$  (Volts)

A similar series of measurements were made with the 1mm hole GEMs, which are summarised in figure 6, again for an induction field of 9kVcm<sup>-1</sup> and a drift field of 100Vcm<sup>-1</sup>. It is noticeable from figures 5 and 6 that the maximum gain obtainable in each gas mixture reduces as the quench gas concentration is increased. As expected the GEM with the 0.5mm hole produces a higher gas gain at a lower voltage across the GEM electrodes. A maximum gas gain of 10<sup>5</sup> was achieved from the 0.5mm hole GEM in a 95:5 gas mixture. Some evidence of an initial charging under illumination has been observed, (a fall in gain of 5% in the first 15mins) but the GEM then stabilises and tracks atmospheric conditions.

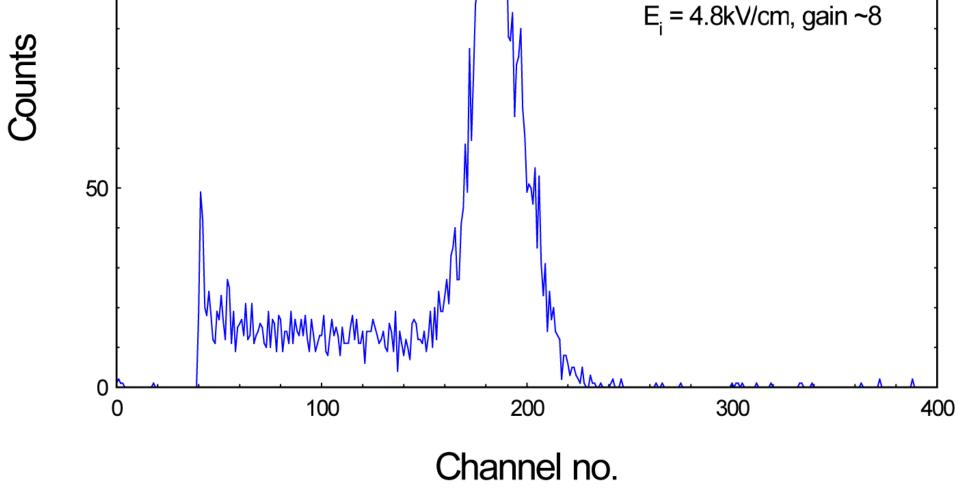
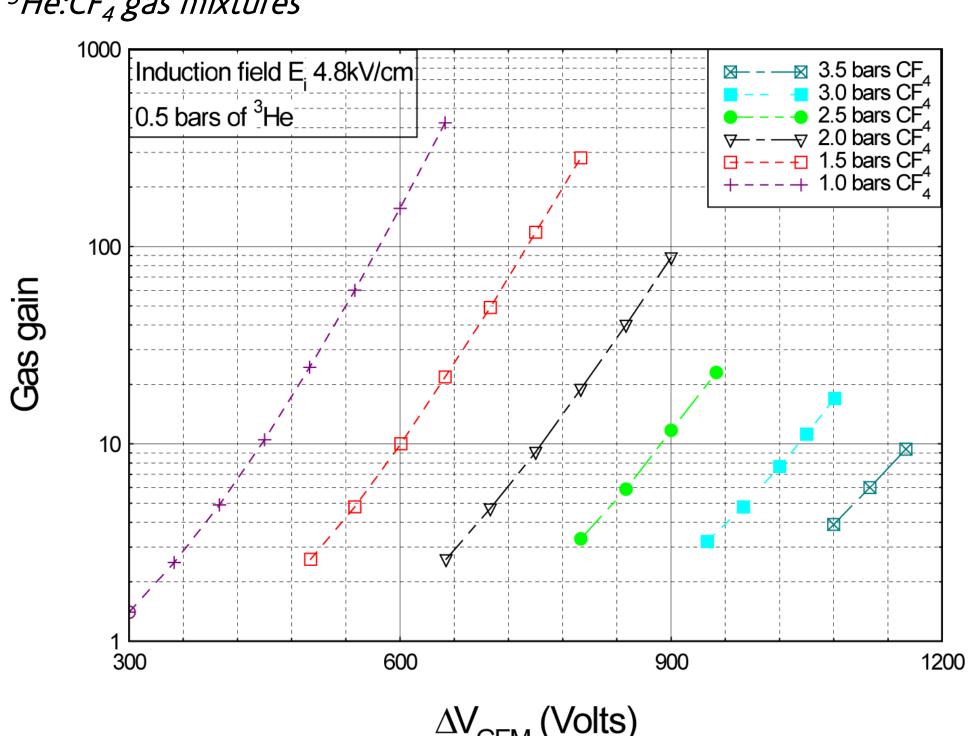


Figure 2 shows a plot of the gain curves obtained for each gas ray spectrum at a gas gain of 580 with the drift field at 100Vcm<sup>-1</sup> and before the onset of a terminal discharge. Our results indicate that kapton GEMs could be operated with resolution of the peak in the spectrum increased by 30%. sufficient gain (~10) at the necessary  $CF_4$  pressure (~2.5 bars) to localise the proton from the <sup>3</sup>He (n, $\alpha$ ) t reaction to 1mm. Figure 4: <sup>55</sup>Fe X-ray spectrum obtained from S8900 GEM with



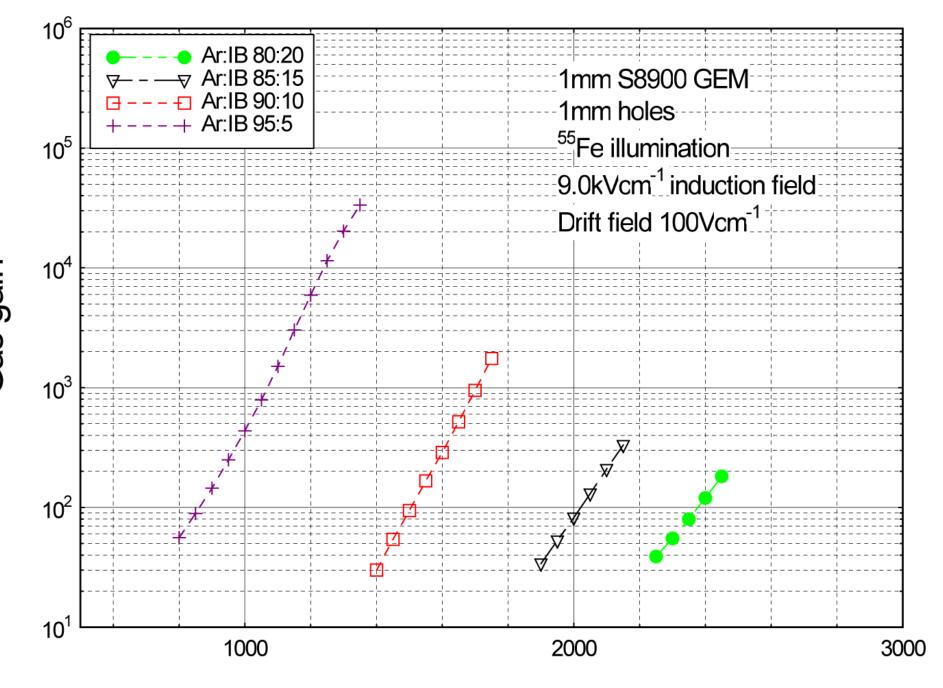
gain The initial measurements were made with the 0.5mm hole structure in a 95:5 mixture of argon and isobutane as this minimised the voltage required across the GEM. Figure 4 shows a typical <sup>55</sup>Fe X-

mixture. The operating point with 4 bars of  $CF_4$  was not attainable the induction field at 9kVcm<sup>-1</sup>. As the drift field is increased to 1kVcm<sup>-1</sup>, the gain reduced by 25% and the FWHM energy

> log-normal fit to peak 1mm S8900 GEM 0.5mm holes Drift voltage -2kV Top of GEM -1.9kV Bottom of GEM -900V Ar:IB 95:5

> > gain 580

Figure 6: Gain curves in various Ar:Isobutane gas mixtures from S8900 GEM with 1.0mm holes

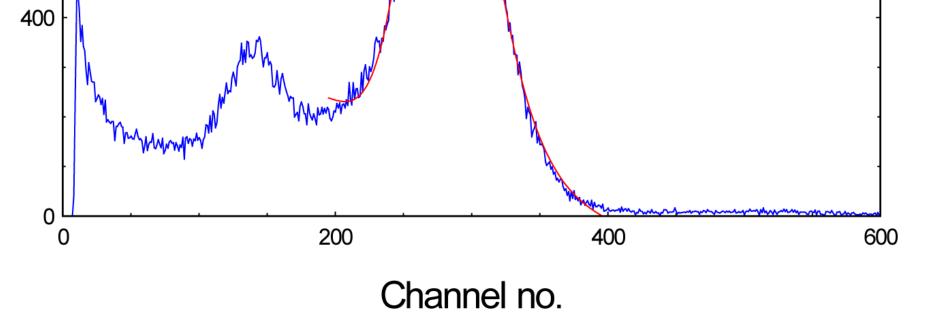


Voltage difference across GEM,  $\Delta V$  (Volts)

### Discussion and future work

Clearly, we are still in the early stages of demonstrating the potential of the GEM detector for applications in ISIS instruments. Whilst we have shown that it is feasible to operate kapton GEMs with sufficient CF<sub>4</sub> to obtain a desired position resolution of 1mm, we need to ensure that this is scalable for larger GEMs.

Figure 2: Gain curves obtained from a kapton GEM in various <sup>3</sup>He:CF<sub>4</sub> gas mixtures



An application of such a large area, 2D GEM detector, would be as a high count rate, high position resolution neutron detector for the reflectometry instruments OffSPEC, PolREF and INTER on the second target station of the ISIS spallation neutron source. Such a device would have a very large impact on the science output of their respective programmes, and could also be exploited worldwide at other neutron scattering institutions.

 $\Delta V_{GFM}$  (Volts)

steadily increased, and also as a function of induction field. A series

Further studies with the S8900 GEMs are required to fully The gas gain was measured as the voltage across the GEM was characterise the stability issues before such a device could be mounted in a pressure vessel in a <sup>3</sup>He:CF<sub>4</sub> atmosphere in order to evaluate its suitability as a thermal neutron detector.

These results have been obtained from GEMs with an area of of measurements were then made as the concentration of quench 10mm by 10mm, which for most of the envisaged applications is too gas was increased, which is summarised in figure 5, for an induction small. Therefore, larger GEMs of 100 by 100mm were obtained field of 9kVcm<sup>-1</sup> and a drift field of 100Vcm<sup>-1</sup>. which are currently being assembled with the intention of repeating the measurements made on the small GEMs.

0.5mm holes

1200

800

Counts

data

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